

AMENDMENTS TO THE SPECIFICATION

Please replace the paragraph beginning on page 19, line 23 and ending on line 28 with the following amended paragraph:

(4) The exposed portions of the film and substrate are etched to form wells in the form of a microwell array. The etching can be performed with, for example, an alkali etching solution (for example, TMAH: tetramethyl ammonium hydroxide) ~~(for example, TMAH: tetramethyl ammonium hydride)~~. In this process, etching advances in the direction of depth of the substrate and beneath the thin film. When etching is conducted for longer than the prescribed time, a lip-shaped protrusion of thin film is formed in the opening of the microwell formed in the silicon substrate.

Please replace the paragraph beginning on page 21, line 1 and ending on line 7 with the following rewritten paragraph:

(4) Wells are formed in microwell array form by etching the exposed portion of the substrate. For example, etching can be conducted with an alkali etching solution (for example, TMAH: tetramethyl ammonium hydroxide) ~~(for example, TMAH: tetramethyl ammonium hydride)~~. When etching is continued in the direction of thickness of the substrate, etching also continues in the area to the sides directly beneath the thin film. When etching is conducted for a period exceeding the conventional period, eave-shaped protrusions of thin film are formed in the entrances to the microwells that have been formed on the silicon plate.

Please replace the paragraph beginning on page 22, line 24 and ending on line 30 with the following amended paragraph:

(4) Wells are formed in microwell array form by etching the exposed portions of the substrate. For example, an alkali etching solution (for example, TMAH: tetramethyl ammonium hydroxide ~~(for example, TMAH: tetramethyl ammonium hydride)~~) is employed in etching. At this time, when etching is conducted in the direction of thickness of the substrate, etching continues to the sides directly beneath the thin film. Here, when etching is conducted beyond the prescribed period, cave-shaped protrusions of thin film are formed in the entrances to the microwells formed on the silicon substrate.

Please replace the paragraph beginning on page 23, line 9 and ending on line 16 with the following rewritten paragraph:

(3) Well etching can be conducted with, for example, an alkali etching solution (such as TMAH: tetramethyl ammonium hydroxide ~~(such as TMAH: tetramethyl ammonium hydride)~~). At this time, the silicon surface into which boron has not diffused etches readily, while the silicon surface where boron has been diffused to high concentration tends not to etch. Thus, etching can proceed selectively in well pattern portions where boron has diffused. When etching is performed in the direction of thickness of the substrate, the etching proceeds to the sides directly beneath the thin film. When etching is conducted beyond the prescribed time, lip-shaped protrusions are formed in the entrances to the microwells formed on the silicon substrate.